FAIRCHILD SEMICONDUCTOR™

October 1997

FDV302P
Digital FET, P-Channel

General Description

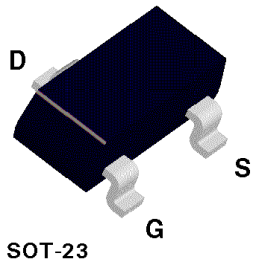
This P-Channel logic level enhancement mode field effect transistor is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for digital transistors. Since bias resistors are not required, this one P-channel FET can replace several digital transistors with different bias resistors such as the DTCx and DCDx series.

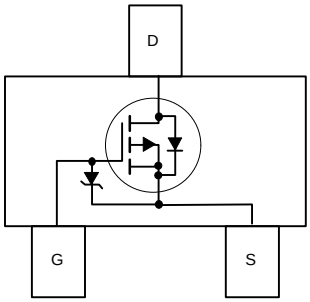
Features

- -25 V, -0.12 A continuous, -0.5 A Peak.
  $R_{DS(ON)}$ = 13 Ω @ V_{GS}= -2.7 V
  $R_{DS(ON)}$ = 10 Ω @ V_{GS} = -4.5 V.
- Very low level gate drive requirements allowing direct operation in 3V circuits. $V_{GS(th)}$ < 1.5V.
- Gate-Source Zener for ESD ruggedness. >6kV Human Body Model
- Compact industry standard SOT-23 surface mount package.
- Replace many PNP digital transistors (DTCx and DCDx) with one DMOS FET.

SOT-23	SuperSOT™-6	SuperSOT™-8	SO-8	SOT-223	SOIC-16

Mark:302





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	FDV302P	Units
V_{DSS}	Drain-Source Voltage	-25	V
V_{GSS}	Gate-Source Voltage	-8	V
I_D	Drain Current - Continuous	-0.12	A
	- Pulsed	-0.5	
P_D	Maximum Power Dissipation	0.35	W
T_J,T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf / 1500 Ohm)	6.0	kV
THERMAL CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

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Electrical Characteristics (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = -250 µA	-25			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	I_D = -250 µA, Referenced to 25 °C		-20		mV /°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -20 V, V_{GS} = 0 V			-1	µA
		T_J = 55°C			-10	µA
I_{GSS}	Gate - Body Leakage Current	V_{GS} = -8 V, V_{DS} = 0 V			-100	nA
ON CHARACTERISTICS (Note)						
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Temp. Coefficient	I_D = -250 µA, Referenced to 25 °C		1.9		mV /°C
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 µA	-0.65	-1	-1.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = -2.7 V, I_D = -0.05 A		10.6	13	Ω
		V_{GS} = -4.5 V, I_D = -0.2 A		7.9	10	
		T_J =125°C		12	18	
$I_{D(ON)}$	On-State Drain Current	V_{GS} = -2.7 V, V_{DS} = -5 V	-0.05			A
g_{FS}	Forward Transconductance	V_{DS} = -5 V, I_D = -0.2 A		0.135		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = -10 V, V_{GS} = 0 V, f = 1.0 MHz		11		pF
C_{oss}	Output Capacitance			7		pF
C_{rss}	Reverse Transfer Capacitance			1.4		pF
SWITCHING CHARACTERISTICS (Note)						
$t_{D(on)}$	Turn - On Delay Time	V_{DD} = -6 V, I_D = -0.2 A, V_{GS} = -4.5 V, R_{GEN} = 50 Ω		5	12	ns
t_r	Turn - On Rise Time			8	16	ns
$t_{D(off)}$	Turn - Off Delay Time			9	18	ns
t_f	Turn - Off Fall Time			5	10	ns
Q_g	Total Gate Charge	V_{DS} = -5 V, I_D = -0.2 A, V_{GS} = -4.5 V		0.22	0.31	nC
Q_{gs}	Gate-Source Charge			0.11		nC
Q_{gd}	Gate-Drain Charge			0.04		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Maximum Continuous Drain-Source Diode Forward Current				-0.2	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = -0.2 A (Note)		-1	-1.5	V

Note:
Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

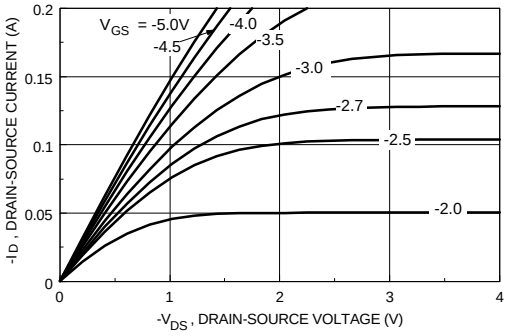

Figure 1. On-Region Characteristics.

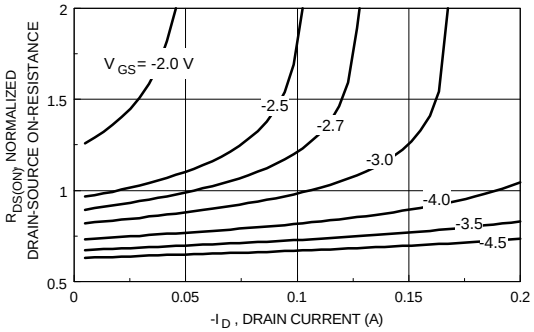

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

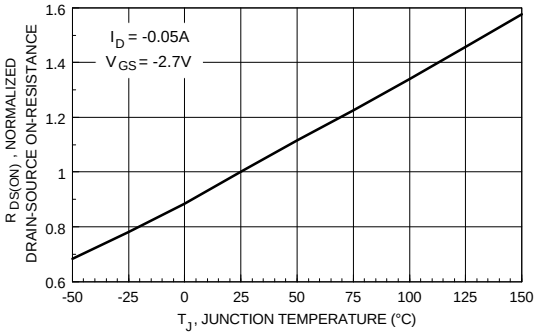

Figure 3. On-Resistance Variation with Temperature.

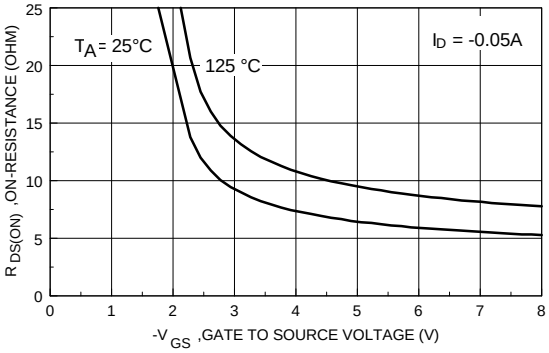

Figure 4. On Resistance Variation with Gate-To- Source Voltage.

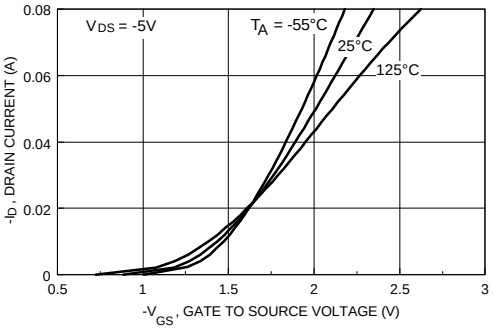

Figure 5. Transfer Characteristics.

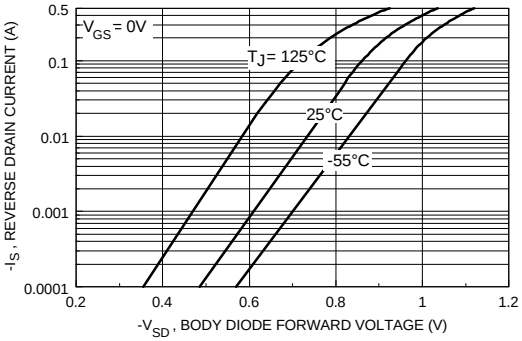

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical And Thermal Characteristics

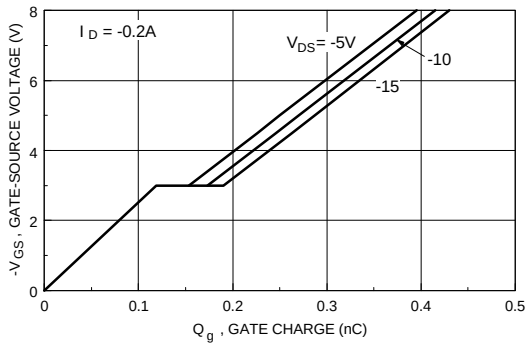

Figure 7. Gate Charge Characteristics.

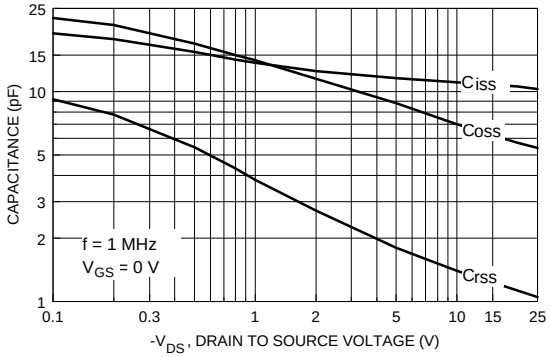

Figure 8. Capacitance Characteristics.

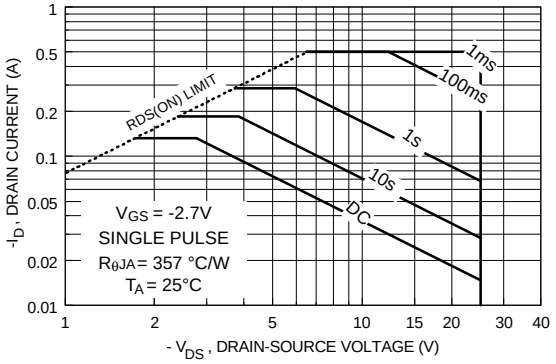

Figure 9. Maximum Safe Operating Area.

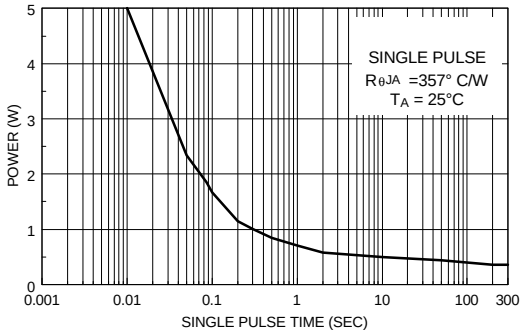

Figure 10. Single Pulse Maximum Power Dissipation.

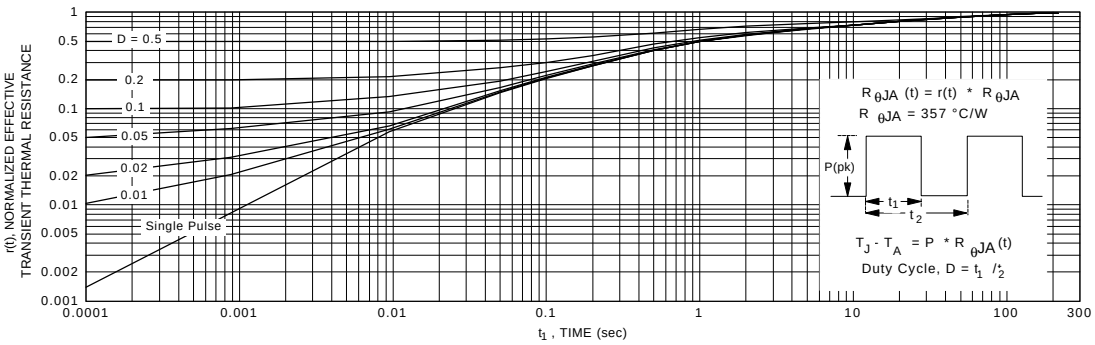

Figure 11. Transient Thermal Response Curve.

Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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